In the claims:

Please amend the claims as follows:

Claims 1-12 (cancelled).

Claim 13 (currently amended) A method of manufacturing a semiconductor device comprising:

forming a heat absorbing layer in an island form over a substrate;

forming an insulating film over said heat absorbing layer;

forming a non-single crystalline semiconductor film on said insulating film;

irradiating said non-single crystalline semiconductor film with light so that said semiconductor film is melted and solidified; and

patterning said semiconductor film into a semiconductor island, ~~the semiconductor island not overlapping with the heat absorbing layer,~~

wherein a channel length direction of the semiconductor island is parallel to a longitudinal outer edge of said heat absorbing layer.

Claims 14 (original) A method according to claim 13 wherein said semiconductor film is crystallized by said light.

Claim 15 (original) A method according to claim 13 wherein said non-single crystalline semiconductor film is selected from an amorphous semiconductor film, a microcrystalline semiconductor film and a polycrystalline semiconductor film.

Claim 16 (original) A method according to claim 13 wherein said semiconductor film comprises silicon.

Claim 17 (original) A method according to claim 15 wherein a plurality of protrusions are formed on said semiconductor film after the irradiation, and a height of said protrusions is at least 30 nm.

Claim 18 (original) A method according to claim 13 wherein said heat absorbing layer comprises a metal selected from the group consisting of Cr, Mo, Ti, Ta and W.

Claim 19 (original) A method according to claim 13 wherein said absorbing layer functions as an electrode of a storage capacitance of a liquid crystal display device or an EL display device.

Claim 20 (currently amended) A method of manufacturing a semiconductor device comprising:

forming a heat absorbing layer comprising a metal over a substrate;

forming a first insulating film over said heat absorbing layer;

forming a non-single crystalline semiconductor film on said first insulating film;

irradiating said non-single crystalline semiconductor film with light to crystallize said semiconductor film wherein said semiconductor film is melted at least partly and a plurality of protrusions are formed on the crystallize semiconductor film;

patterning the crystallized semiconductor film into at least one semiconductor island to form a channel region; ~~, the semiconductor island not overlapping with the heat absorbing layer;~~

forming a gate insulating film on the semiconductor island; and

forming a gate electrode on said gate insulating film,

wherein a longitudinal edge of said heat absorbing layer is approximately parallel to a channel length direction of said semiconductor island.

Claim 21 (previously amended) A method according to claim 20 wherein said heat absorbing layer comprises a metal selected from the group consisting of Cr, Mo, Ti, Ta and W.

Claim 22 (currently amended) A method of manufacturing a semiconductor device comprising:

forming a heat absorbing layer comprising a metal over a substrate;

forming a first insulating film over said heat absorbing layer;

forming a non-single crystalline semiconductor film on said first insulating film;

irradiating said non-single crystalline semiconductor film with light to crystallize said semiconductor film wherein said semiconductor film is melted at least partly and a plurality of protrusions are formed on the crystallize semiconductor film;

patterning the crystallized semiconductor film into at least one semiconductor island having a channel region therein; ~~, the semiconductor island not overlapping with the heat absorbing layer;~~

forming a gate insulating film on the semiconductor island; and

forming a gate electrode on said gate insulating film,

wherein a longitudinal edge of the heat absorbing layer is parallel to a channel length direction of the semiconductor island, and

wherein said protrusions are formed so that first regions of said channel region has a larger number of said protrusions and second regions of said channel region has no or a smaller number of said protrusions, and said first and second regions appear in turn in a direction orthogonal to the channel length direction of the semiconductor island.

Claim 23 (previously amended) A method according to claim 22 wherein said heat absorbing layer comprises a metal selected from the group consisting of Cr, Mo, Ti, Ta and W.

Claim 24 (previously amended) A method according to claim 22 wherein said a height of said protrusions is at least 30 nm.

Claim 25 (original) A method according to claim 22 further comprising a step of crystallizing said non-single crystalline semiconductor film before irradiating said light.

Claim 26 (original) A method according to claim 22 wherein said light is a laser light.

Claim 27 (original) A method according to claim 20 wherein said light is a laser light.

Claim 28 (original) The method according to claim 20 wherein said semiconductor device is selected from a personal computer, a video camera, a portable information terminal, an electronic game equipment, and a digital camera.

Claim 29 (original) The method according to claim 20 wherein said semiconductor device is a liquid crystal device.

Claim 30 (original) The method according to claim 20 wherein said semiconductor device is an EL display device.

Claim 31 (original) The method according to claim 22 wherein said semiconductor device is selected from a personal computer, a video camera, a portable information terminal, an electronic game equipment, and a digital camera.

Claim 32 (original) The method according to claim 22 wherein said semiconductor device is a liquid crystal device.

Claim 33 (original) The method according to claim 22 wherein said semiconductor device is an EL display device.

Claim 34 (New) The method according to claim 20 wherein said channel region does not overlap said heat absorbing layer.

Claim 35 (New) The method according to claim 22 wherein said channel region does not overlap said heat absorbing layer.